



Ruttonsha International Rectifier Ltd.

SILICON RECTIFIER

HIGH POWER RECTIFIER DIODE

Type : R5800K 02CS...06CS SERIES

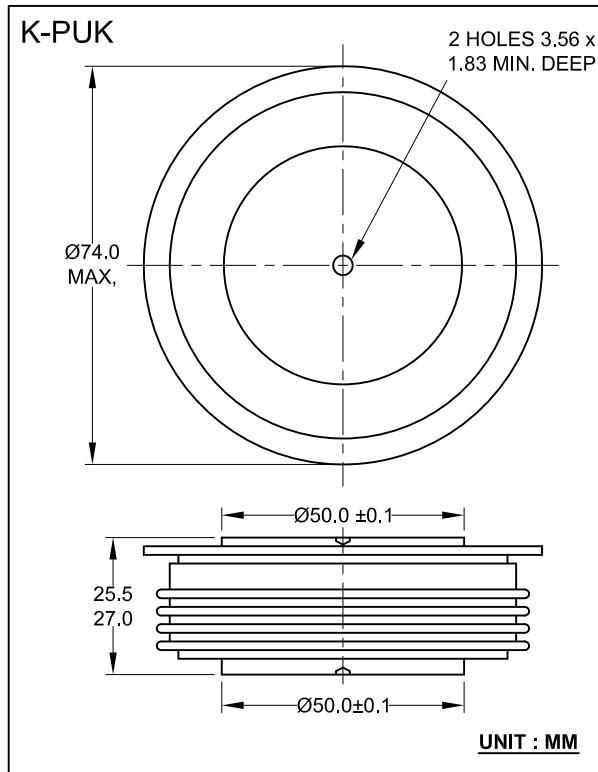
Features

- * Low voltage rating up to 600V
- * High current capability
- * Low forward recovery
- * Press-puk encapsulation
- * Case style conform to (K-PUK)

Typical Applications

- * Snubber diode for GTO
- * High Voltage free-wheeling diode

Hockey Puk Version



MAJOR RATING & CHARACTERISTICS

Parameters	R5800K..06CS	Units
I _{F(AV)}	5880	A
@ Ths	58	°C
I _{F(RMS)} @ 55°C	9240	A
I _{FSM} @ 50Hz	81000	A
V _{RRM} Range	200 to 600	V
I ² t	32800	10 ³ A ² s
T _J max,	-40°C to 180°	°C

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ELECTRICAL SPECIFICATION

VOLTAGE RATINGS

Type Number	Voltage Code	V_{RRM} max. repetitive peak reverse voltage V	V_{RSM} max. Non-repetitive peak reverse voltage	I_{RRM} max. @ $T_J = T_{J\ Max.}$ mA
R5800K...06CS	02	200	300	100
	04	400	500	
	06	600	700	

FORWARD CONDUCTION

Parameter	R5800K...06CS	Unit	Conditions	
I_F (AV) Max, average forward current @ Heatsink temp.	5880	A	180° conduction, half sine wave Double side cooled	
	58	°C		
I_F (RMS)	9240	A	@ 55°C heat sink temperature double side cooled	
I_{FSM}	81000	A	$t - 10ms$	sinusoidal half wave, Initial $T_J = T_{J\ max.}$
I^2t	32800	$10^3 A^2s$	$t = 0.1$ to 10ms. no voltage reapplied	
V_F (TO)	0.7	V	$T_J = T_{J\ max.}$	
r_f	0.04	$m\Omega$	$T_J = T_{J\ max.}$	
V_{FM}	0.90	V	$I_{pk} = 4000A, T_J = T_{J\ max}, t_p = 10ms$ sinusoidal wave	

Thermal and Mechanical Specification

Parameter	R5800K 06CS	Unit	Conditions	
T_J	Max, Junction operating temperature	-40 to 180	°C	
T_{stg}	Max, storage temperature range	-40 to 180	°C	
R_{thJ-C}	Max, Thermal resistance, junction to case	0.0160	°C/W	DC operation double side cooled
F	Mounting Force, ±10%	24 to 30	kN	
W_t	Approximate weight	500	g	
Case style	(K-PUK)		See Outline Table	